

## MDD3754RH Datasheet

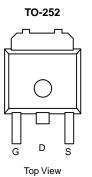
# P-Channel 40 V (D-S) MOSFET

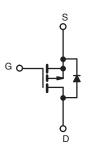
PRODUCT SUMMARY			
V <sub>DS</sub> (V)	-40		
$R_{DS(on)}\left(\Omega\right)$ at $V_{GS}$ = -10 V	0.012		
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS}$ = -4.5 V	0.015		
I <sub>D</sub> (A)	-50		
Configuration	Single		

### FEATURES

- TrenchFET<sup>®</sup> power MOSFET
- Package with low thermal resistance
- 100 %  $R_g$  and UIS tested







P-Channel MOSFET

ABSOLUTE MAXIMUM RATING	<b>S</b> (T <sub>C</sub> = 25 °C, unles	s otherwise noted	)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V <sub>DS</sub>	-40	V	
Gate-Source Voltage		V <sub>GS</sub>	± 20	v	
Continuous Drain Current	T <sub>C</sub> = 25 °C <sup>a</sup>	I	-50		
Continuous Drain Current	T <sub>C</sub> = 125 °C	Ι <sub>D</sub>	-39		
Continuous Source Current (Diode Conducti	on) <sup>a</sup>	I <sub>S</sub>	-50	А	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	-200		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	-40		
Single Pulse Avalanche Energy	L = 0.1 MH	E <sub>AS</sub>	80	mJ	
	T <sub>A</sub> = 25 °C		3		
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	PD	136	W	
	T <sub>C</sub> = 125 °C		45		
Operating Junction and Storage Temperatur	e Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	50	°C/W
Junction-to-Case (Drain)		R <sub>thJC</sub>	1.1	0/10

#### Notes

a. Package limited.

- b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square PCB (FR4 material).

d. Parametric verification ongoing.

<b>SPECIFICATIONS</b> ( $T_C = 25 \ ^{\circ}C_{,}$	, unless otherv	vise noted)					
PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static					•	•	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> =	= 0 V, I <sub>D</sub> = -250 μA	-40	-	-	v
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = -250 \ \mu A$		-1.5	-	-2.5	v
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = -40 V	-	-	-1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS} = -40 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	-50	μA
		$V_{GS} = 0 V$	$V_{DS}$ = -40 V, $T_J$ = 175 °C	-	-	-150	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = -10 V	$V_{DS} \le -5 V$	-50	-	-	А
		V <sub>GS</sub> = -10 V	I <sub>D</sub> = -17 A	-	0.012	-	Ω
Ducia Courses On Otota Desistances		$V_{GS} = -10 \text{ V}$	I <sub>D</sub> = -50 A, T <sub>J</sub> = 125 °C	-	0.017	-	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -50 A, T <sub>J</sub> = 175 °C	-	0.020	-	
		$V_{GS} = -4.5 V$	I <sub>D</sub> = -14 A	-	0.015	-	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> =	15 V, I <sub>D</sub> = -17 A	_	61	-	S
Dynamic <sup>b</sup>		<u>.</u>				•	
Input Capacitance	C <sub>iss</sub>			-	2872	3950	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = -25 V, f = 1 MHz	-	508	635	pF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	352	440	
Total Gate Charge <sup>c</sup>	Qg			-	60	80	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = -10 V	$V_{DS} = -30 \text{ V}, I_D = -50 \text{ A}$	-	5.7	8.6	nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	14.7	22	
Gate Resistance	Rg		f = 1 MHz	1.5	3	4.5	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			_	10	15	
Rise Time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> =	-20 V, $R_L$ = 0.4 Ω	-	12	18	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	I <sub>D</sub> ≅ -50 A,	$V_{\text{GEN}} = -10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$	-	40	60	ns
Fall Time <sup>c</sup>	t <sub>f</sub>			-	16	24	1
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	-200	А
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> =	-50 A, V <sub>GS</sub> = 0 V	-	-1	-1.5	V
							4

#### Notes

a. Pulse test; pulse width  $\leq 300~\mu\text{s},~\text{duty}~\text{cycle} \leq 2~\%.$ 

b. Guaranteed by design, not subject to production testing.

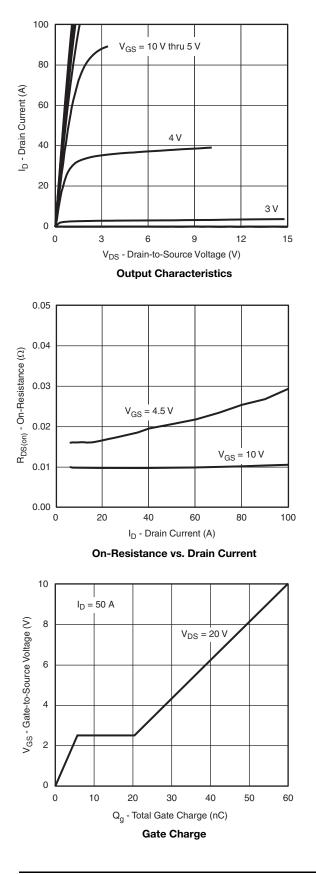
c. Independent of operating temperature.

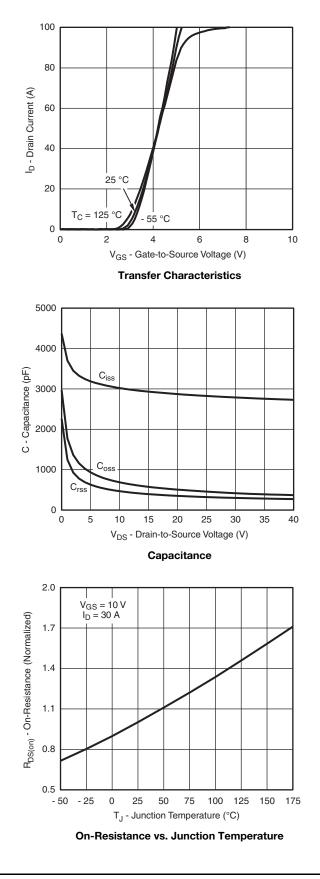
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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## **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)

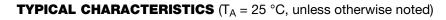


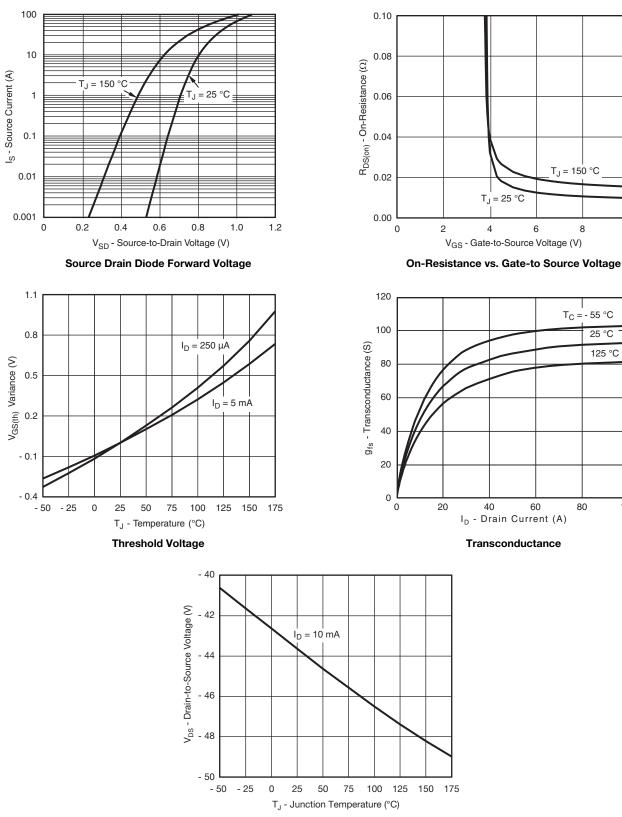


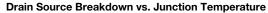


10

100

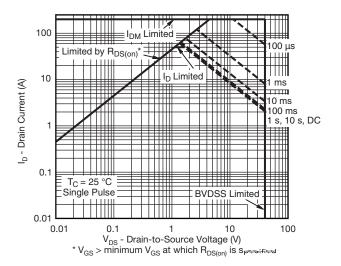




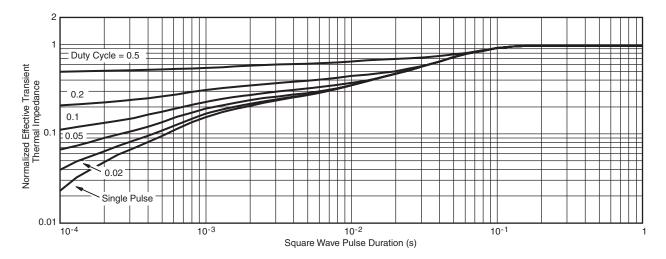




## **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)

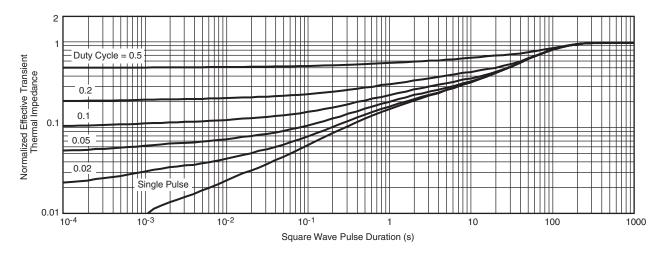


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case





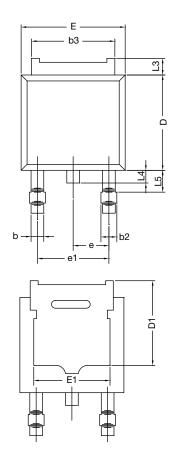
#### Normalized Thermal Transient Impedance, Junction-to-Ambient

#### Note

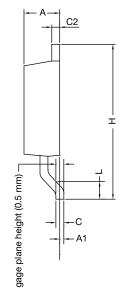
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.





# **TO-252AA Case Outline**



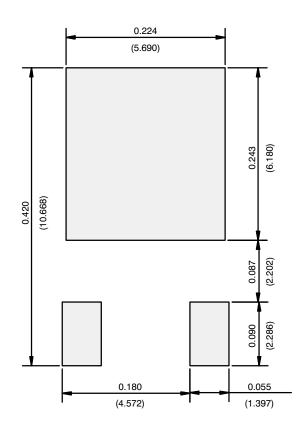
N.   18   -   64   76   95   46   47	MAX.   2.38   0.127   0.88   1.14   5.46   0.61   0.89   6.22	MIN.   0.086   -   0.025   0.030   0.195   0.018   0.018	MAX.   0.094   0.005   0.035   0.045   0.215   0.024   0.035
- 64 76 95 46 46 97	0.127 0.88 1.14 5.46 0.61 0.89	- 0.025 0.030 0.195 0.018 0.018	0.005 0.035 0.045 0.215 0.024
76 95 46 46 97	0.88 1.14 5.46 0.61 0.89	0.030 0.195 0.018 0.018	0.035 0.045 0.215 0.024
76 95 46 46 97	1.14 5.46 0.61 0.89	0.030 0.195 0.018 0.018	0.045 0.215 0.024
95 46 46 97	5.46 0.61 0.89	0.195 0.018 0.018	0.215 0.024
46 46 97	0.61 0.89	0.018	0.024
46 97	0.89	0.018	
97			0.035
-	6.22		1
		0.235	0.245
10	-	0.161	-
35	6.73	0.250	0.265
32	-	0.170	-
40	10.41	0.370	0.410
2.28 BSC		0.090	BSC
4.56 BSC		0.180	) BSC
40	1.78	0.055	0.070
89	1.27	0.035	0.050
-	1.02	-	0.040
	1.52	0.040	0.060
	4.56 40 89 - 01	40 1.78 89 1.27 - 1.02	40 1.78 0.055 89 1.27 0.035 - 1.02 -

Note

• Dimension L3 is for reference only.



## **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)



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